

ABSTRACT OF THE DISCLOSURE

Disclosed is a method for manufacturing a gallium nitride-based semiconductor light emitting device, including the 5 steps of sequentially forming, over a substrate, a first conductivity type clad layer, an active layer, and a second conductivity type clad layer, forming a transparent electrode over the second conductivity type clad layer, forming a photoresist film on the transparent electrode such that the 10 transparent electrode is exposed at a predetermined region corresponding to one lateral end portion thereof, removing respective portions of the transparent electrode, second conductivity type clad layer, and active layer corresponding to the predetermined region, thereby partially exposing the first 15 conductivity type clad layer, removing the photoresist film, and forming first and second bonding electrodes on predetermined portions of the transparent electrode and second conductivity type clad layer, respectively. In accordance with this method, it is possible to simplify the whole process, to easily form a 20 transparent electrode pattern suitable to prevention of electrostatic discharge (ESD), and to prevent a degradation in the bonding force of a transparent electrode caused by residual photoresist.